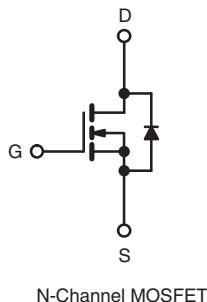
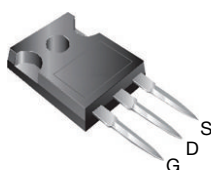


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.21
Q_g (Max.) (nC)	180	
Q_{gs} (nC)	61	
Q_{gd} (nC)	85	
Configuration	Single	

TO-247AC


FEATURES

- Superfast body diode eliminates the need for external diodes in ZVS applications
- Lower gate charge results in simpler drive requirements
- Enhanced dV/dt capabilities offer improved ruggedness
- Higher gate voltage threshold offers improved noise immunity
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

APPLICATIONS

- Zero voltage switching (SMPS)
- Telecom and server power supplies
- Uninterruptible power supplies
- Motor control applications

ORDERING INFORMATION

Package	TO-247AC
Lead (Pb)-free	IRFP26N60LPbF
	SiHFP26N60L-E3
SnPb	IRFP26N60L
	SiHFP26N60L

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A
		$T_C = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current ^a	I_{DM}	100	
Linear Derating Factor		3.8	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ^b	E_{AS}	570	mJ
Repetitive Avalanche Current ^a	I_{AR}	26	A
Repetitive Avalanche Energy ^a	E_{AR}	47	mJ
Maximum Power Dissipation	P_D	470	W
Peak Diode Recovery dV/dt ^c	dV/dt	21	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^d	for 10 s	300	
Mounting Torque	6-32 or M3 screw	10	lbf · in
		1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 1.7\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 26\text{ A}$, dV/dt = 21 V/ns (see fig. 12).
- $I_{SD} \leq 26\text{ A}$, dI/dt $\leq 480\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.27	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$		-	0.33	-	V/ $^{\circ}\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		3.0	-	5.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	50	μA
		$V_{DS} = 480\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$		-	-	2.0	mA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}^b$	-	0.21	0.25	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 16\text{ A}$		13	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5		-	5020	-	pF
Output Capacitance	C_{oss}			-	450	-	
Reverse Transfer Capacitance	C_{rss}			-	34	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 0\text{ V to } 480\text{ V}^c$	-	230	-	
Effective Output Capacitance (Energy related)	$C_{oss\text{ eff. (ER)}}$			-	170	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 26\text{ A}$, $V_{DS} = 480\text{ V}$, see fig. 7 and 15 ^b	-	-	180	nC
Gate-Source Charge	Q_{gs}			-	-	61	
Gate-Drain Charge	Q_{gd}			-	-	85	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}$, $I_D = 26\text{ A}$, $R_g = 4.3\text{ }\Omega$, $V_{GS} = 10\text{ V}$ see fig. 11a and 11b ^b		-	31	-	ns
Rise Time	t_r			-	110	-	
Turn-Off Delay Time	$t_{d(off)}$			-	47	-	
Fall Time	t_f			-	42	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	26	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	100	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 26\text{ A}$, $V_{GS} = 0\text{ V}^b$		-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = 26\text{ A}$		-	170	250	ns
		$T_J = 125\text{ }^{\circ}\text{C}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$		-	210	320	
Body Diode Reverse Recovery Charge	Q_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = 26\text{ A}$, $V_{GS} = 0\text{ V}^b$		-	670	1000	nC
		$T_J = 125\text{ }^{\circ}\text{C}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$		-	1050	1570	
Reverse Recovery Current	I_{RRM}	$T_J = 25\text{ }^{\circ}\text{C}$		-	7.3	11	A
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
 $C_{oss\text{ eff. (ER)}}$ is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

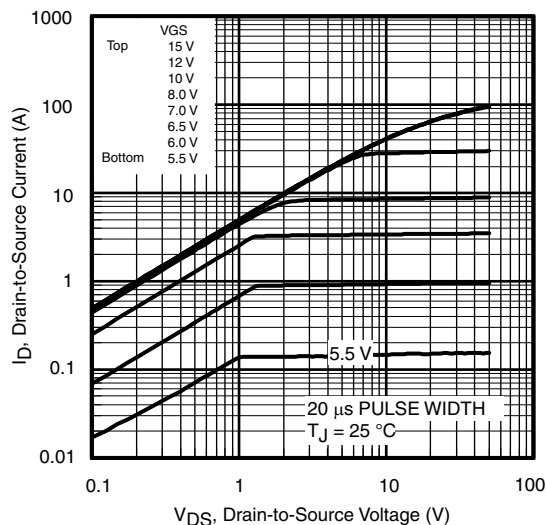


Fig. 1 - Typical Output Characteristics

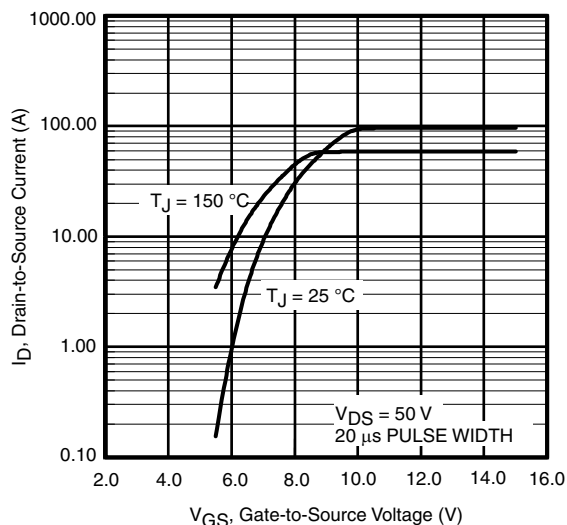


Fig. 3 - Typical Transfer Characteristics

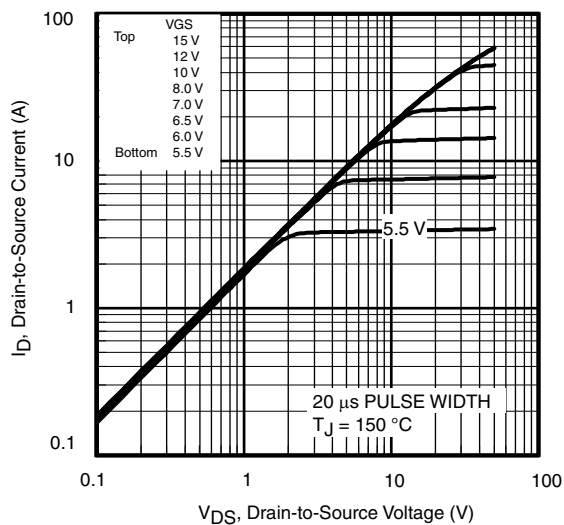


Fig. 2 - Typical Output Characteristics

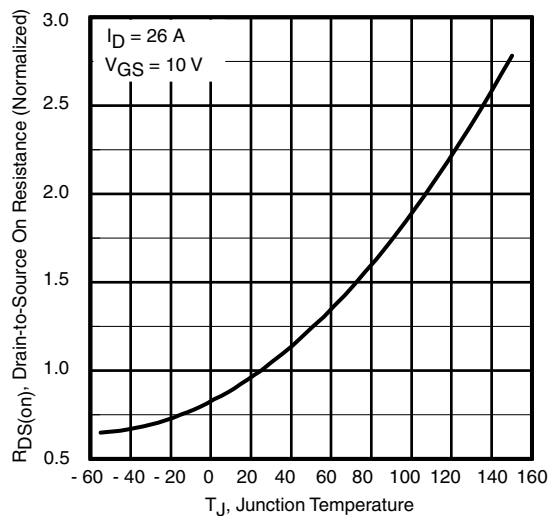
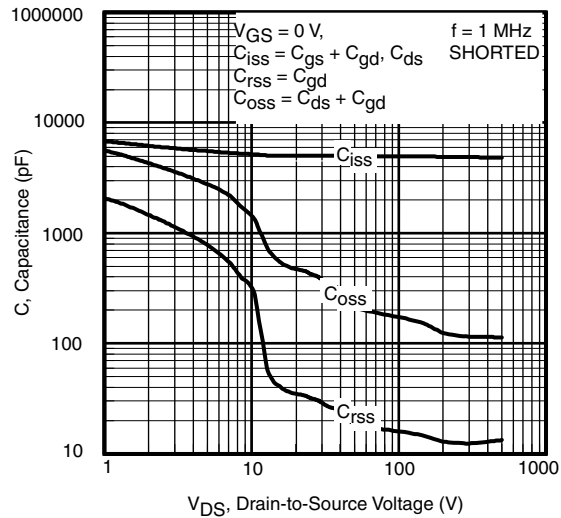
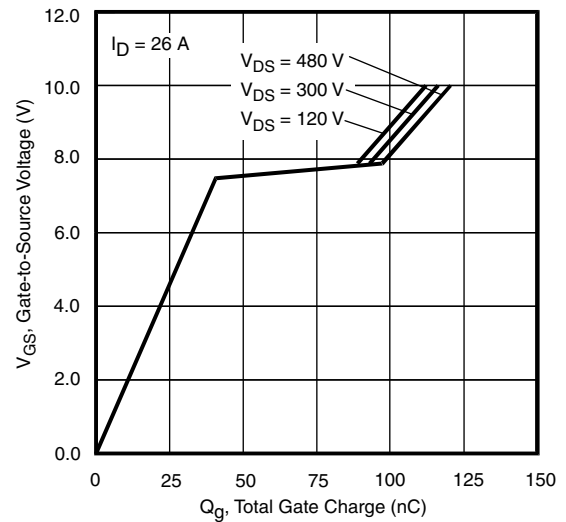
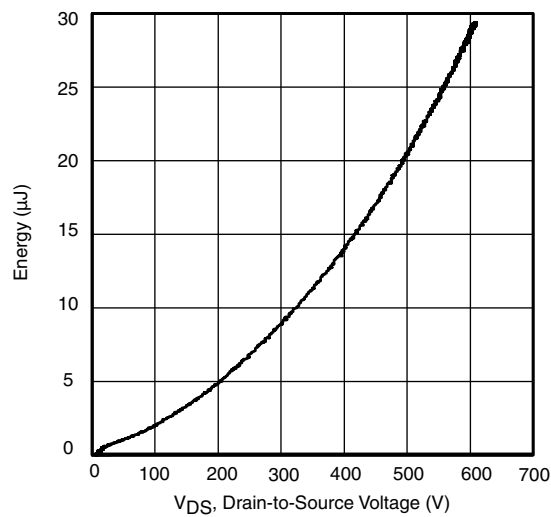
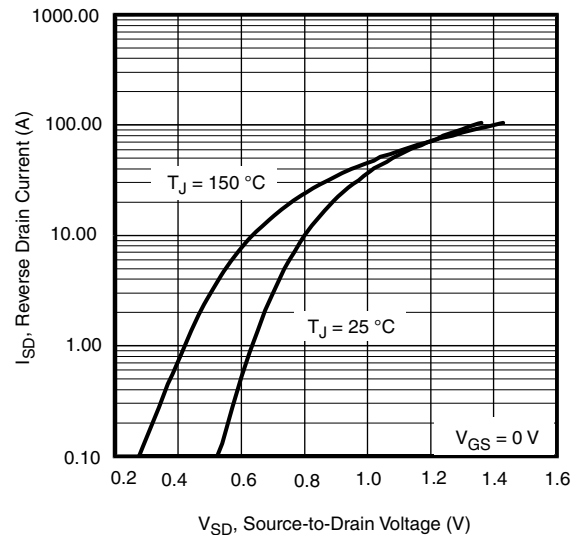


Fig. 4 - Normalized On-Resistance vs. Temperature


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 6 - Typical Output Capacitance Stored Energy vs. V_{DS}

Fig. 8 - Typical Source-Drain Diode Forward Voltage

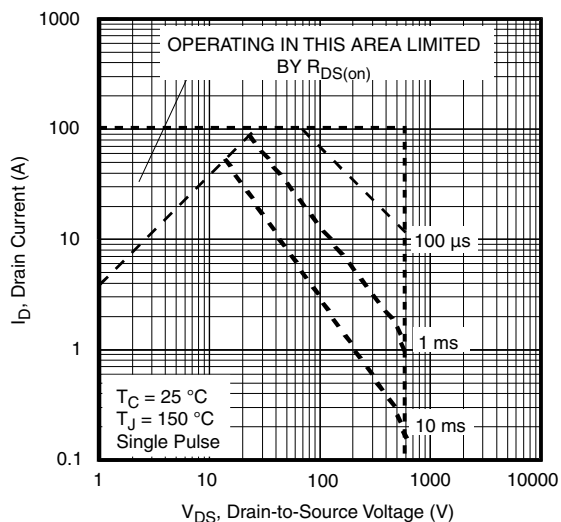


Fig. 9 - Maximum Safe Operating Area

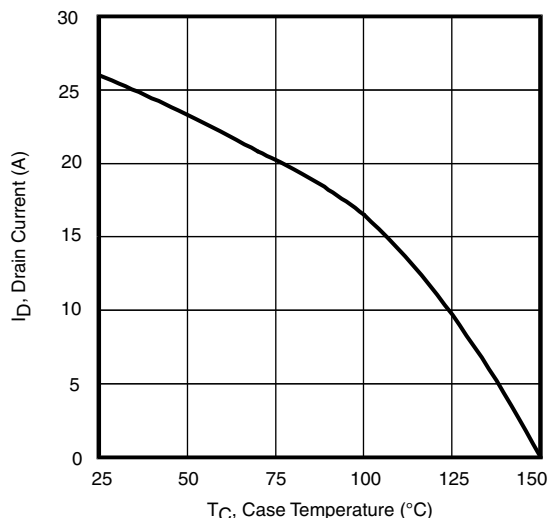


Fig. 10 - Maximum Drain Current vs. Case Temperature

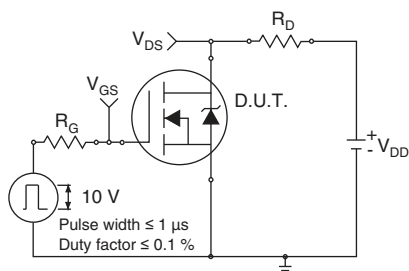


Fig. 11a - Switching Time Test Circuit

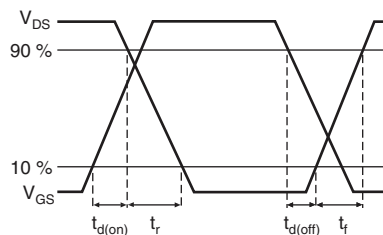


Fig. 11b - Switching Time Waveforms

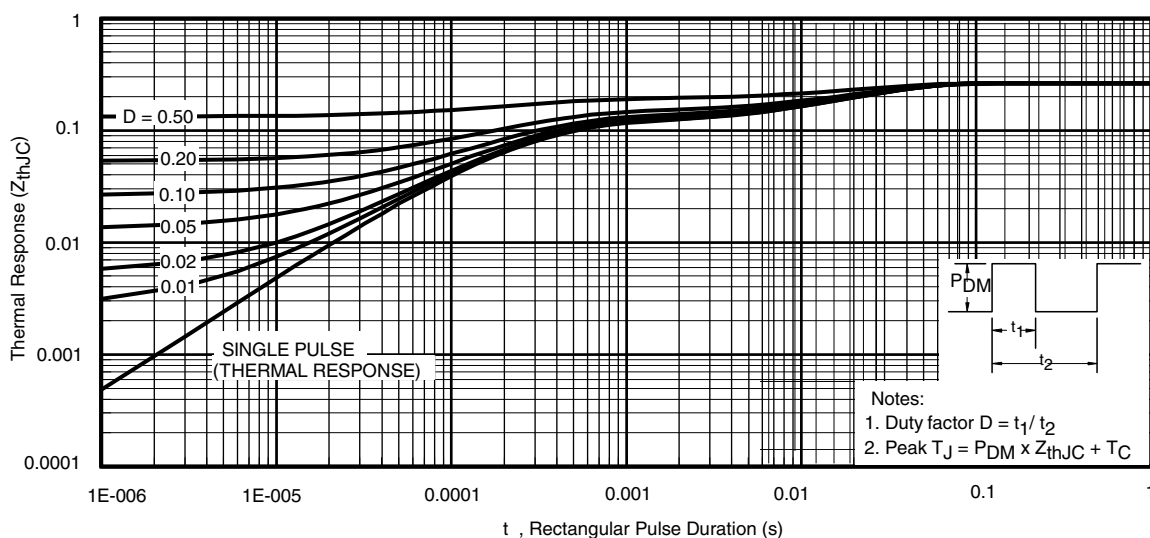
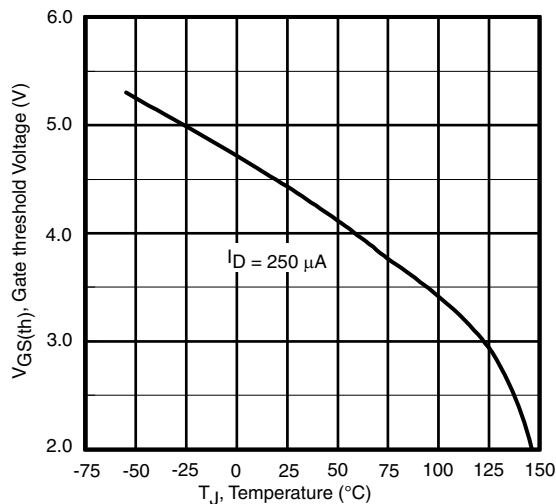
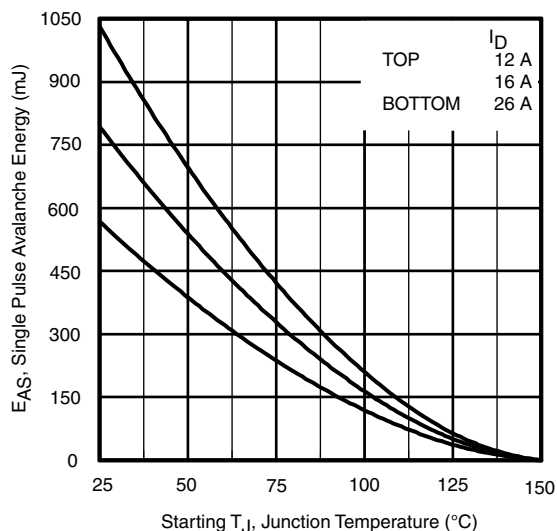
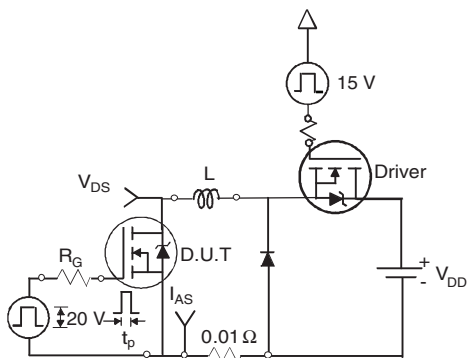
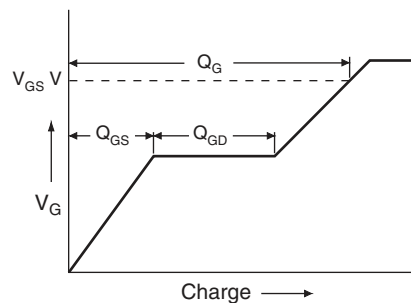
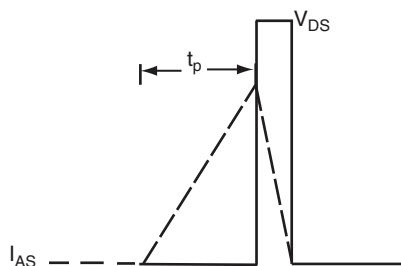
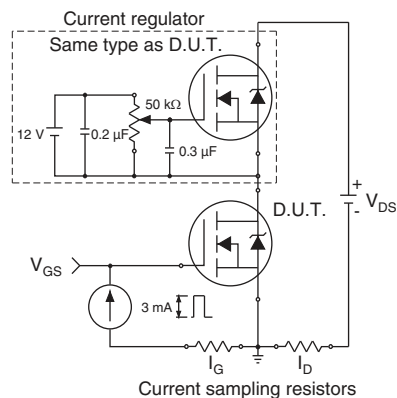
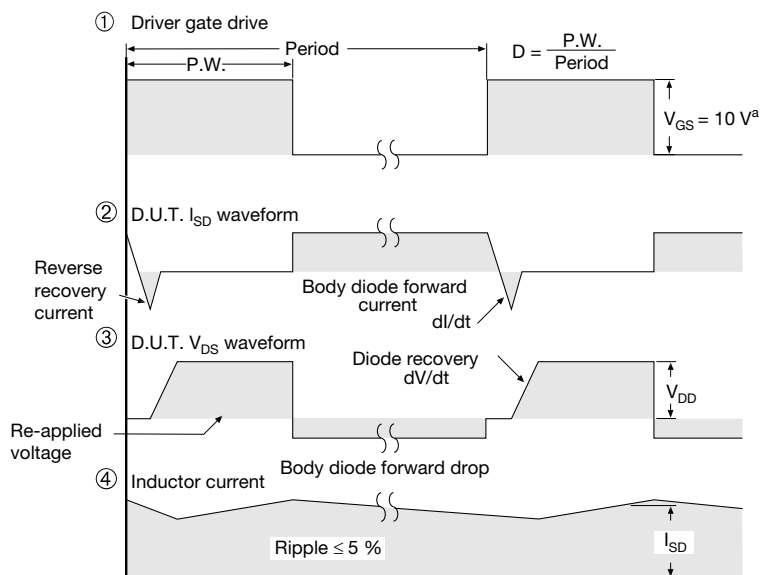
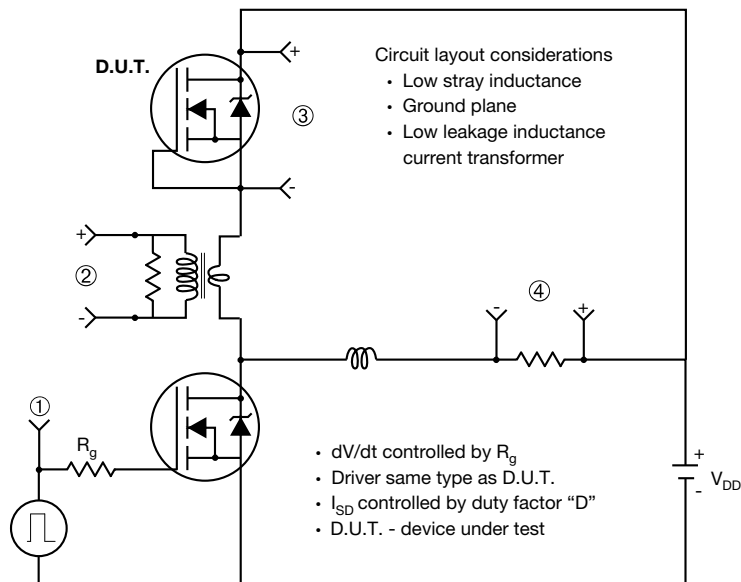


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 13 - Threshold Voltage vs. Temperature

Fig. 14c - Maximum Avalanche Energy vs. Drain Current

Fig. 14a - Unclamped Inductive Test Circuit

Fig. 15a - Basic Gate Charge Waveform

Fig. 14b - Unclamped Inductive Waveforms

Fig. 15b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 16 - For N-Channel

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TO-247AC (High Voltage)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

ECN: X13-0103-Rev. D, 01-Jul-13
DWG: 5971

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.
8. Xian and Mingxin actually photo.





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